

IV1Q12050T3 – 1200V 50mΩ SiC MOSFET

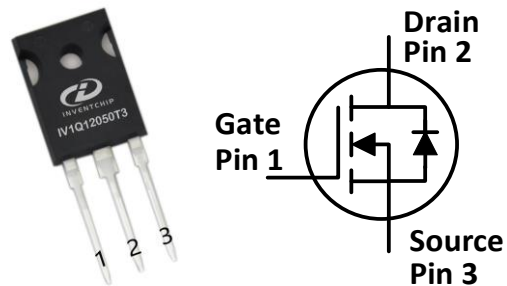
Features:

- High blocking voltage with low on-resistance
- High speed switching with low capacitance
- High operating junction temperature capability
- Very fast and robust intrinsic body diode

Applications:

- Solar inverters
- UPS
- Motor drivers
- High voltage DC/DC converters
- Switch mode power supplies

Package:



Part Number	Package
IV1Q12050T3	TO247-3

Absolute Maximum Ratings (T_c=25°C unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V _{DS}	Drain-Source voltage	1200	V	V _{GS} =0V, I _D =100μA	
V _{GS}	Gate-Source voltage	-5 to 20	V	Recommended maximum	
I _D	Drain current (continuous)	58	A	V _{GS} =20V, T _C =25°C	Fig. 21
		43	A	V _{GS} =20V, T _C =100°C	
I _{DM}	Drain current (pulsed)	145	A	Pulse width limited by SOA	Fig. 24
P _{TOT}	Total power dissipation	327	W	T _C =25°C	Fig. 22
T _{stg}	Storage temperature range	-55 to 175	°C		
T _J	Operating junction temperature	-55 to 175	°C		
T _L	Solder Temperature	260	°C	Wave soldering only allowed at leads, 1.6mm from case for 10 s	

Thermal Data

Symbol	Parameter	Value	Unit	Note
R _{θ(j-c)}	Thermal Resistance from Junction to Case	0.459	°C/W	Fig. 23

Electrical Characteristics ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value			Unit	Test Conditions	Note
		Min.	Typ.	Max.			
I_{DSS}	Zero gate voltage drain current		5	100	μA	$V_{DS}=1200\text{V}, V_{GS}=0\text{V}$	
I_{GSS}	Gate leakage current		1	± 100	nA	$V_{DS}=0\text{V}, V_{GS}=-5\sim 20\text{V}$	
V_{TH}	Gate threshold voltage		3.2		V	$V_{GS}=V_{DS}, I_D=6\text{mA}$	Fig. 8, 9
			2.2			$V_{GS}=V_{DS}, I_D=6\text{mA}$ @ $T_c=175^\circ\text{C}$	
R_{ON}	Static drain-source on-resistance		50	65	$\text{m}\Omega$	$V_{GS}=20\text{V}, I_D=20\text{A}$ @ $T_j=25^\circ\text{C}$	Fig. 4, 5, 6, 7
			80		$\text{m}\Omega$	$V_{GS}=20\text{V}, I_D=20\text{A}$ @ $T_j=175^\circ\text{C}$	
C_{iss}	Input capacitance		2770		pF	$V_{DS}=800\text{V}, V_{GS}=0\text{V},$ $f=1\text{MHz}, V_{AC}=25\text{mV}$	Fig. 16
C_{oss}	Output capacitance		110		pF		
C_{rss}	Reverse transfer capacitance		10		pF		
E_{oss}	C_{oss} stored energy		45		μJ		Fig. 17
Q_g	Total gate charge		120		nC	$V_{DS}=800\text{V}, I_D=20\text{A},$ $V_{GS}=-5\text{ to }20\text{V}$	Fig. 18
Q_{gs}	Gate-source charge		25		nC		
Q_{gd}	Gate-drain charge		48		nC		
R_g	Gate input resistance		2.8		Ω	$f=1\text{MHz}$	
E_{ON}	Turn-on switching energy		877		μJ	$V_{DS}=800\text{V}, I_D=30\text{A},$ $V_{GS}=-2\text{ to }20\text{V},$ $R_{G(\text{ext})}=3.3\Omega,$ $L=450\mu\text{H}$	Fig. 19, 20
E_{OFF}	Turn-off switching energy		211		μJ		
$t_{d(\text{on})}$	Turn-on delay time		31		ns		
t_r	Rise time		22				
$t_{d(\text{off})}$	Turn-off delay time		22				
t_f	Fall time		19				

Reverse Diode Characteristics ($T_c=25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value			Unit	Test Conditions	Note
		Min.	Typ.	Max.			
V_{SD}	Diode forward voltage		4.9		V	$I_{SD}=20\text{A}, V_{GS}=0\text{V}$	Fig. 10, 11, 12
			4.4		V	$I_{SD}=20\text{A}, V_{GS}=0\text{V},$ $T_J=175^\circ\text{C}$	
t_{rr}	Reverse recovery time		44.4		ns	$V_{GS}=-2\text{V}/+20\text{V},$ $I_{SD}=30\text{A}, V_R=800\text{V},$ $di/dt=1000\text{A}/\mu\text{s},$	
Q_{rr}	Reverse recovery charge		212.6		nC	$R_{G(\text{ext})}=10\Omega$	
I_{RRM}	Peak reverse recovery current		10.8		A	$L=450\mu\text{H}$	

Typical Performance (curves)

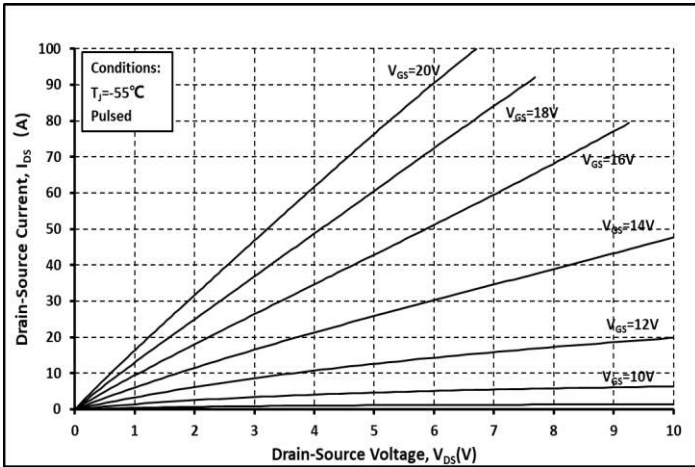


Fig. 1 Output Curve @ $T_j = -55^\circ\text{C}$

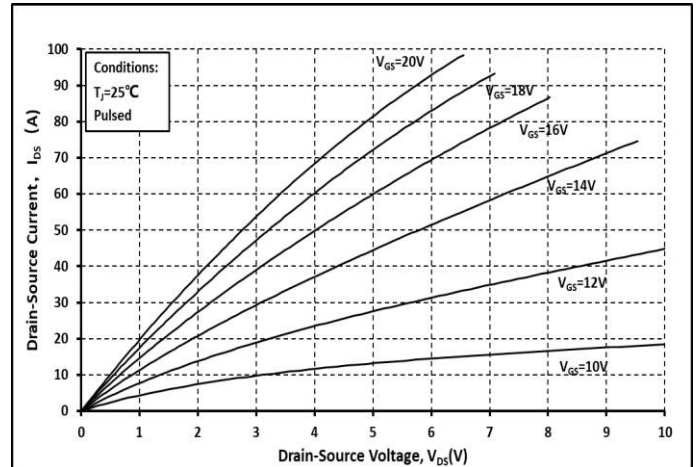


Fig. 2 Output Curve @ $T_j = 25^\circ\text{C}$

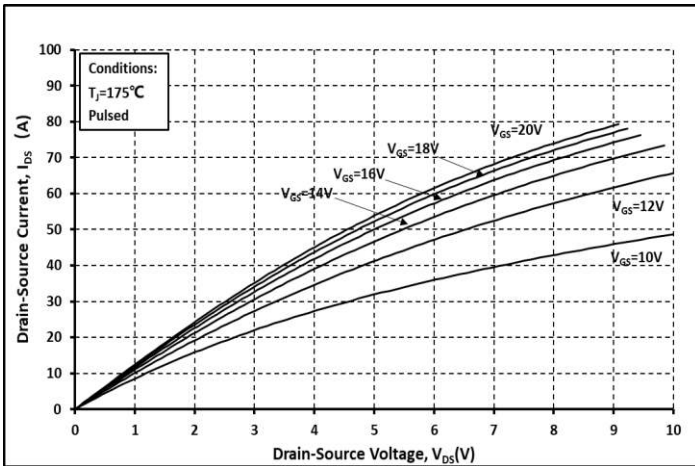


Fig. 3 Output Curve @ $T_j = 175^\circ\text{C}$

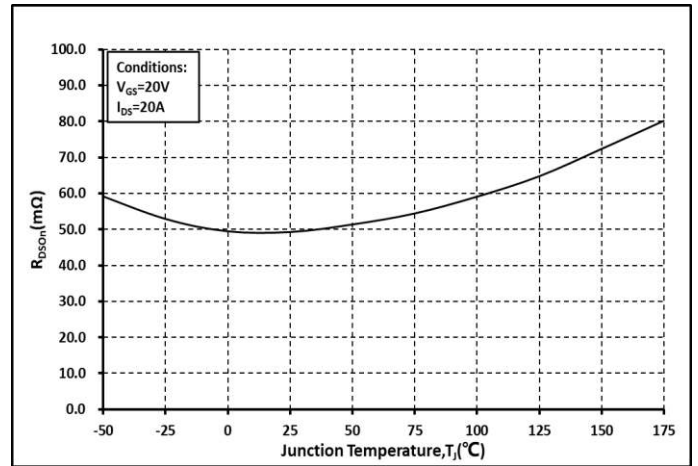


Fig. 4 $R_{DS(on)}$ vs. Temperature

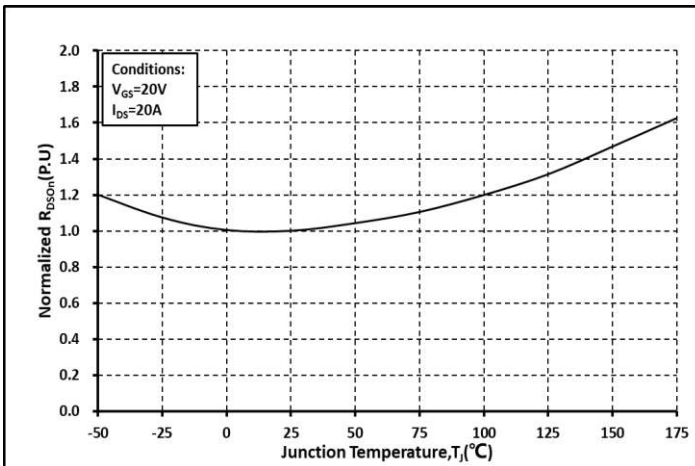


Fig. 5 Normalized $R_{DS(on)}$ vs. Temperature

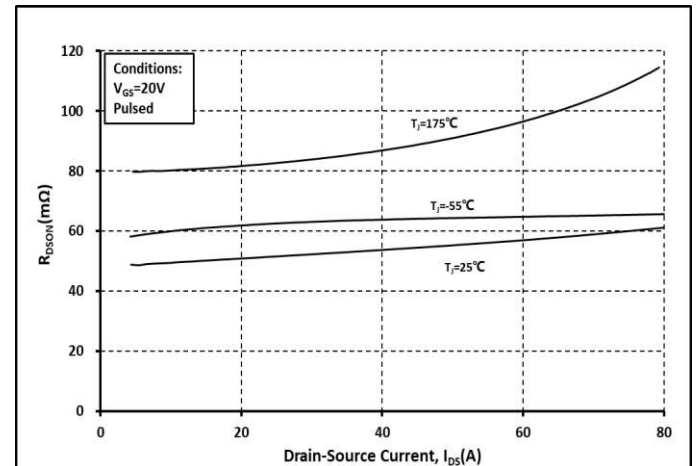


Fig. 6 $R_{DS(on)}$ vs. I_{DS} @ Various Temperature

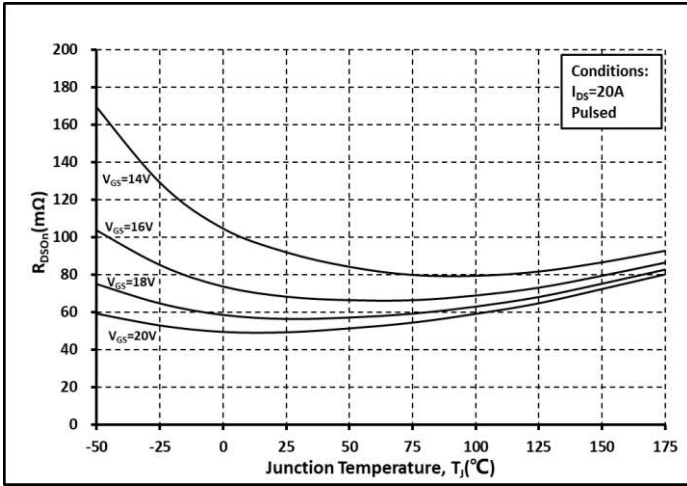


Fig. 7 Ron vs. Temperature @ Various V_{GS}

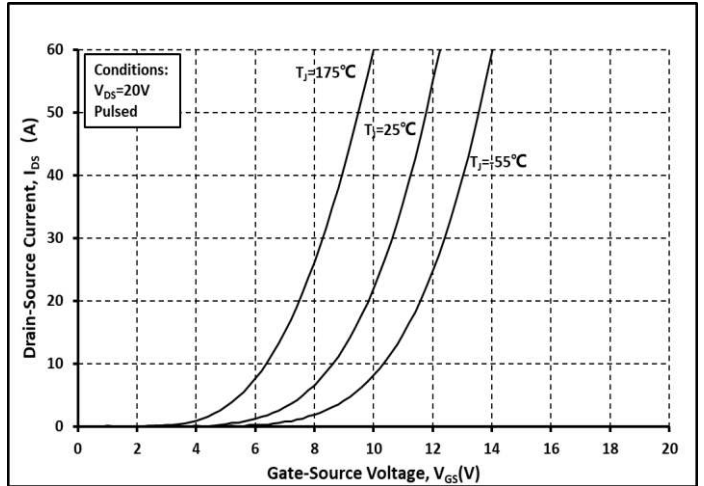


Fig. 8 Transfer Curves @ Various Temperature

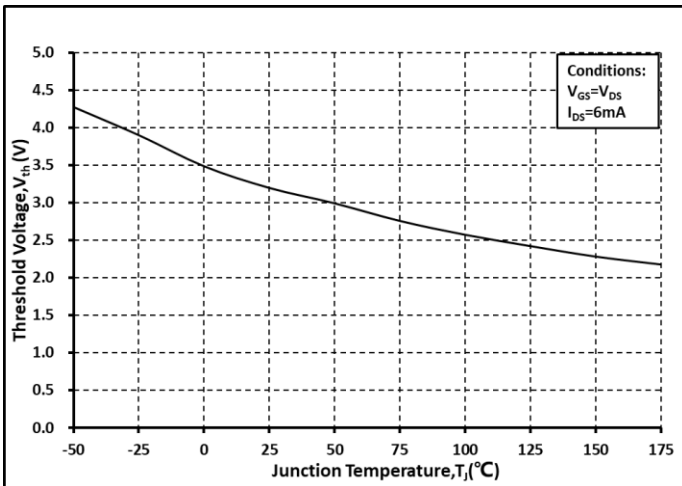


Fig. 9 Threshold Voltage vs. Temperature

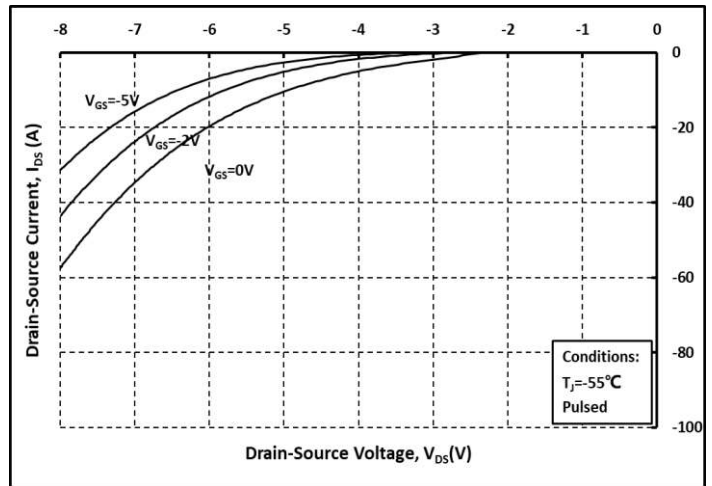


Fig. 10 Body Diode Curves @ $T_J=-55^\circ C$

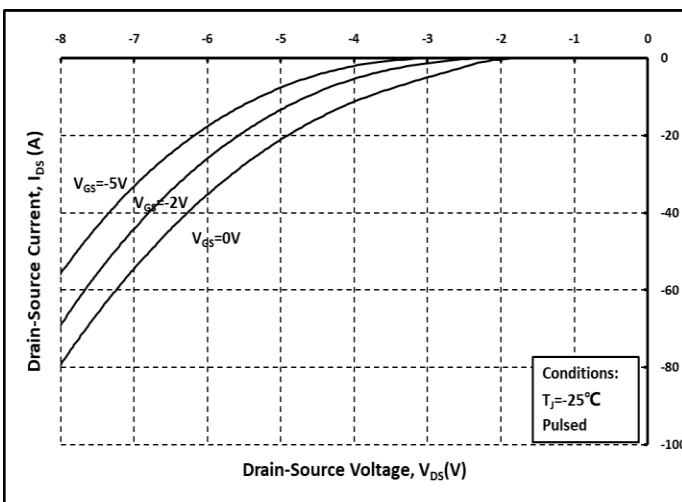


Fig. 11 Body Diode Curves @ $T_J=25^\circ C$

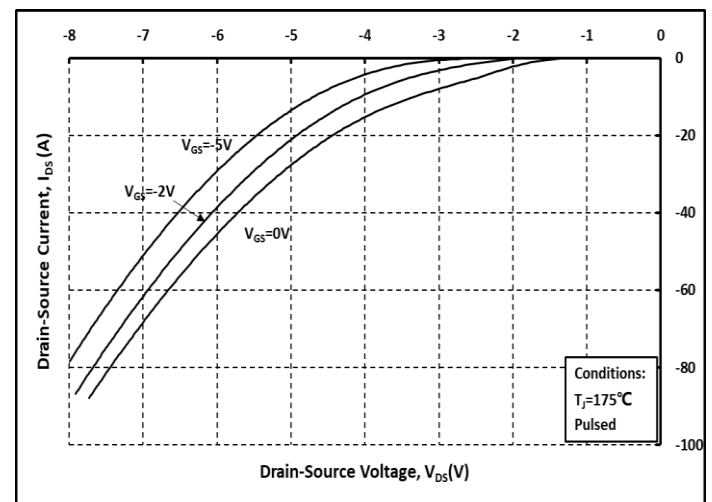


Fig. 12 Body Diode Curves @ $T_J=175^\circ C$

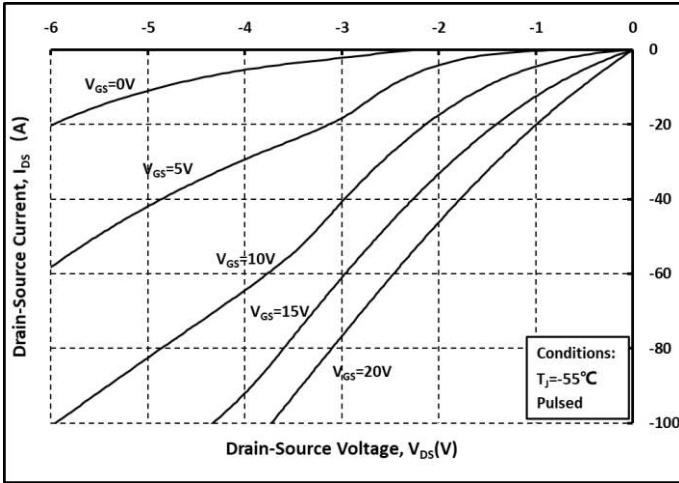


Fig. 13 3rd Quadrant Curves @ $T_j = -55^\circ\text{C}$

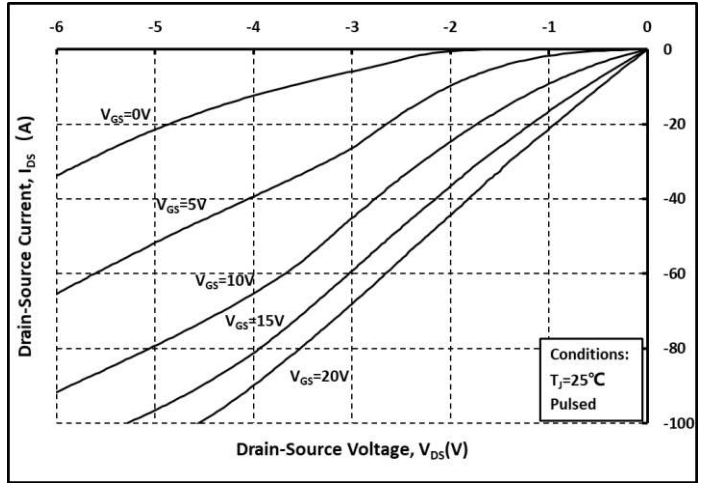


Fig. 14 3rd Quadrant Curves @ $T_j = 25^\circ\text{C}$

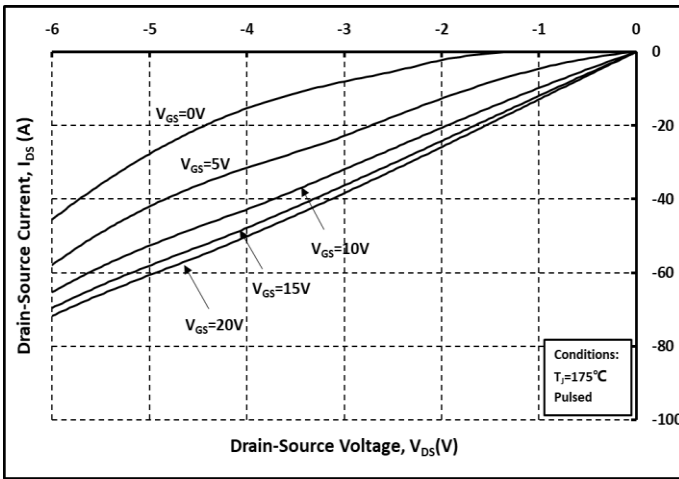


Fig. 15 3rd Quadrant Curves @ $T_j = 175^\circ\text{C}$

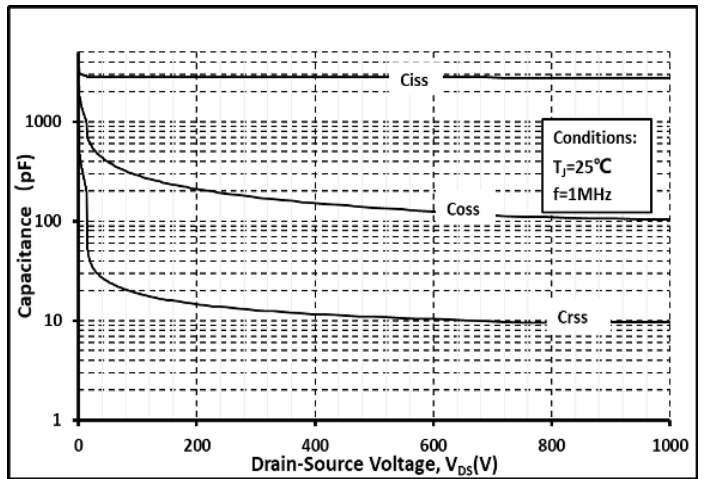


Fig. 16 Capacitance vs. V_{DS}

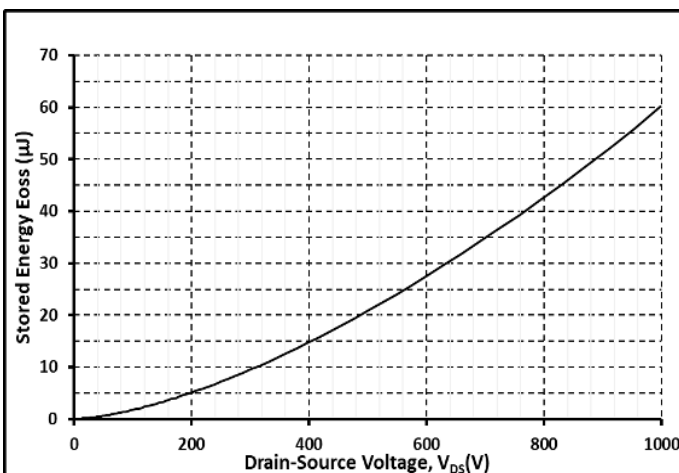


Fig. 17 Output Capacitor Stored Energy

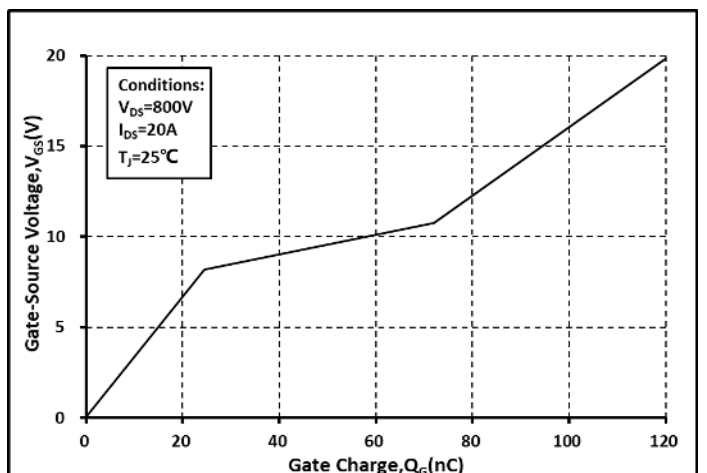


Fig. 18 Gate Charge Characteristics

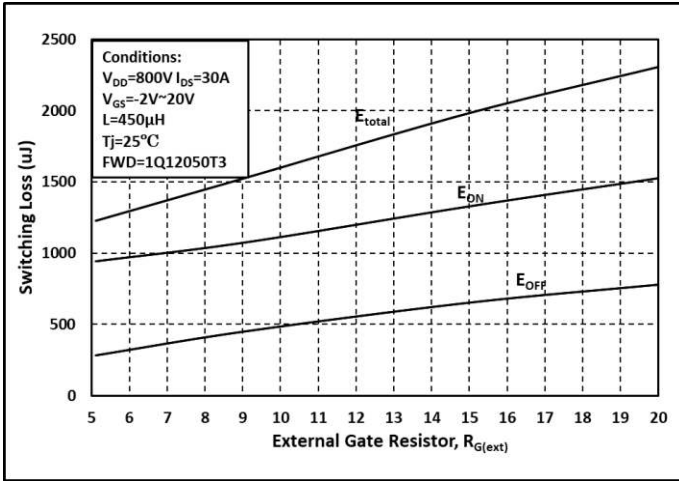


Fig. 19 Switching Energy vs. $R_{G(ext)}$

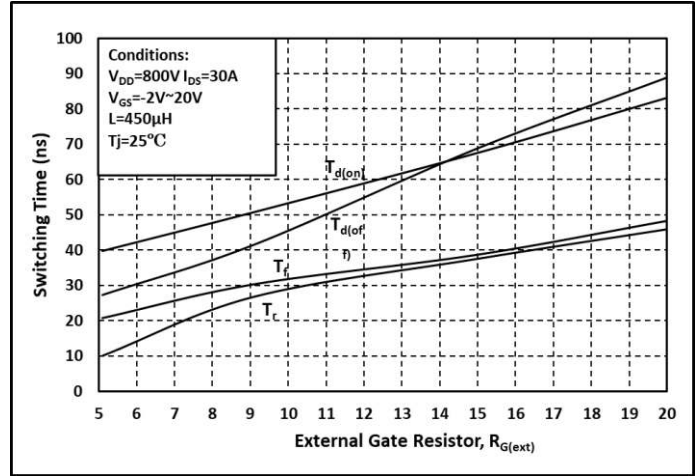


Fig. 20 Switching Times vs. $R_{G(ext)}$

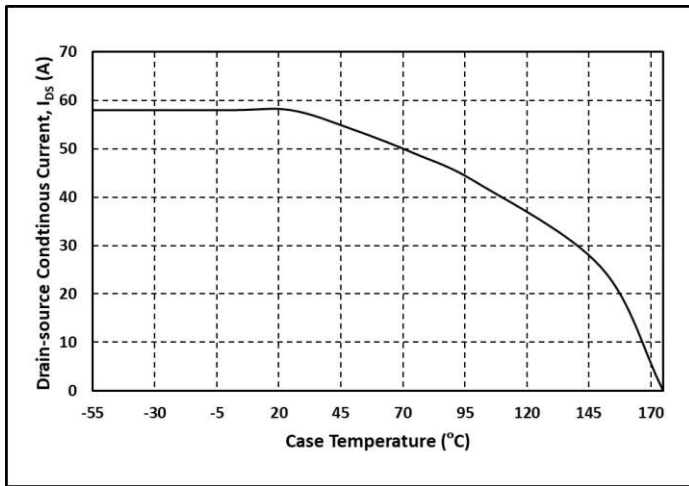


Fig. 21 Continuous Drain Current vs. Case Temperature

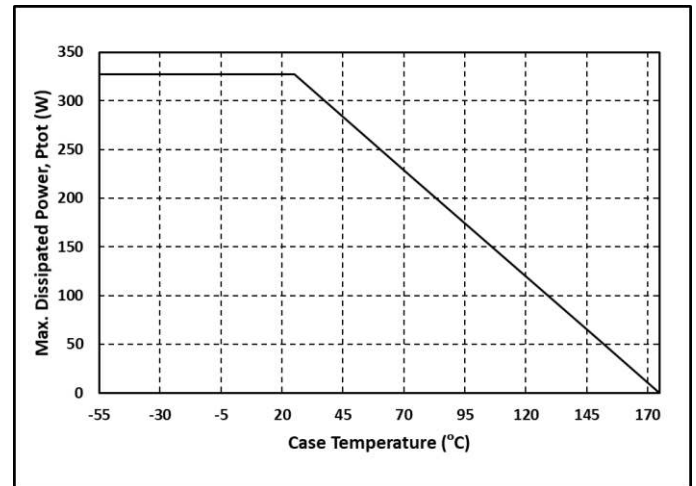


Fig. 22 Max. Power Dissipation Derating vs. Case Temperature

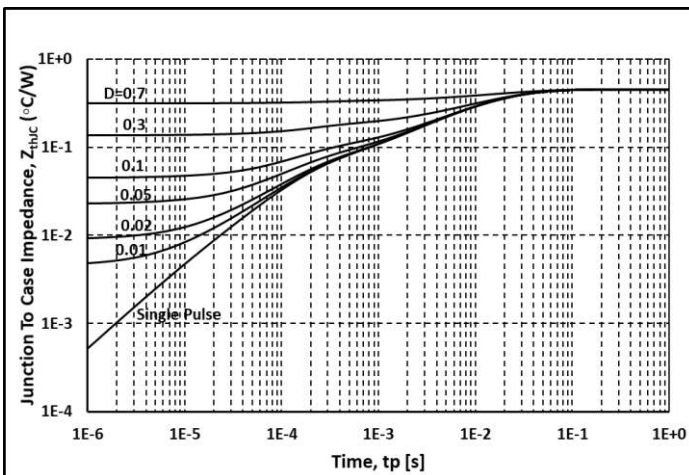


Fig. 23 Thermal Impedance

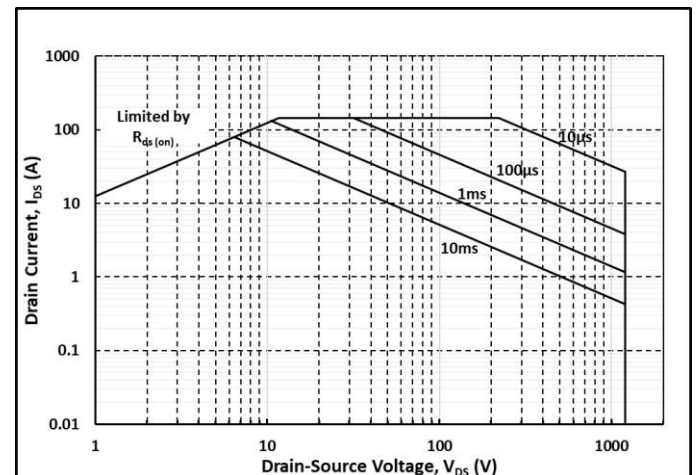
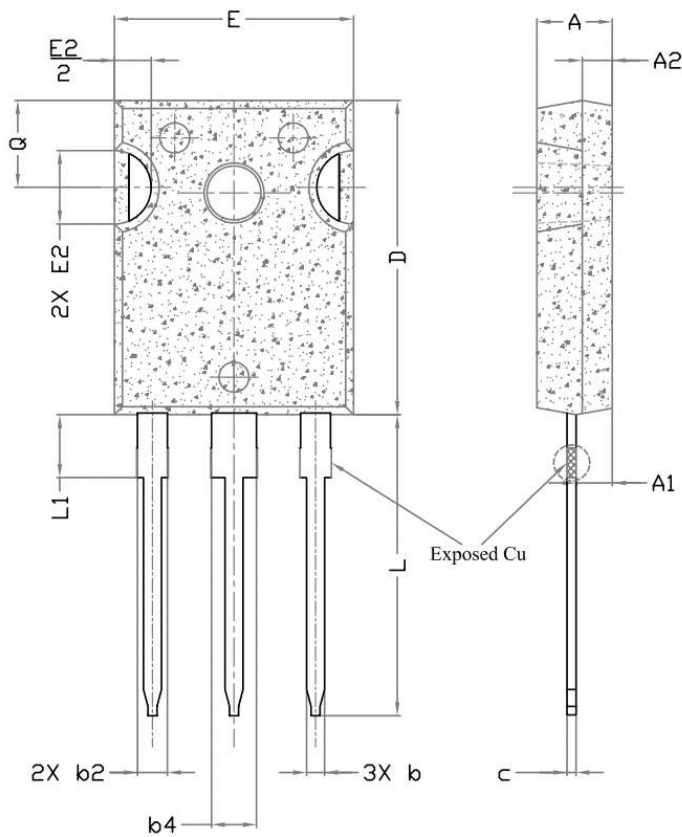
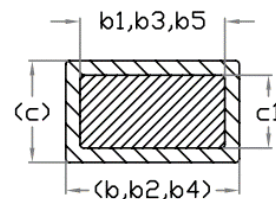
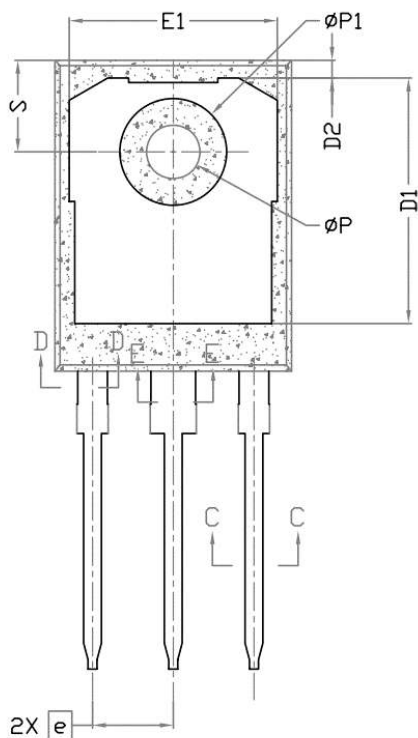


Fig. 24 Safe Operating Area

Package Dimensions



SYMBOL	DIMENSIONS			NOTES
	MIN.	NOM.	MAX.	
A	4.83	5.02	5.21	
A1	2.29	2.41	2.55	
A2	1.50	2.00	2.49	
b	1.12	1.20	1.33	
b1	1.12	1.20	1.28	
b2	1.91	2.00	2.39	6
b3	1.91	2.00	2.34	
b4	2.87	3.00	3.22	6, 8
b5	2.87	3.00	3.18	
c	0.55	0.60	0.69	6
c1	0.55	0.60	0.65	
D	20.80	20.95	21.10	4
D1	16.25	16.55	17.65	5
D2	0.51	1.19	1.35	
E	15.75	15.94	16.13	4
E1	13.46	14.02	14.16	5
E2	4.32	4.91	5.49	3
e	5.44BSC			
L	19.81	20.07	20.32	
L1	4.10	4.19	4.40	6
∅P	3.56	3.61	3.65	7
∅P1	7.19REF.			
Q	5.39	5.79	6.20	
S	6.04	6.17	6.30	



Section C--C,D--D,E--E

Note:

1. Package Reference: JEDEC TO247, Variation AD
2. All Dimensions are in mm
3. Slot Required, Notch May Be Rounded
4. Dimension D&E Do Not Include Mold Flash

Notes

Current revision is preliminary one, for further information please contact IVCT's Office.
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